



Aktuelles Experiment:

noname.rcp

Modellbeschreibung

Number	Layer Name	Thickness [nm]	Refr. Index	Fitted
			[632.8 nm]	
0	Air	-	1.000	no
1	NoName0	39.40	1.446	yes
2	Silicon DUV-N	IR -	3.874	no

Fit parameter

Fit parameter	Fit result
[1,1] NoName0: Thickness [nm]	39.40
NoName0: N0	1.436

All parameter

Parameter	Value
[1] Wavelength [nm]	632.8
[1] Angle [°]	70.00
[1] Time [s]	0.0
[1] Temperature [°C]	23.5
[1] Sample rotation [°]	0.00
[1] Depol. D0	1.0000
[1] Depol. D1	0.0000
[1] Depol. D2	0.0000
[1] Beam diameter	4.00
[1] Aperture diameter	4.00
[1,1] Thickness variation	10.0
[1] Wavelength resolution (nm)	0.0
[1] Angle variation	3.0
[1] Angle offset [°]	0.00
[1] Wavelength Offset (nm)	0.00
[1] Wavelength Linear	1.00000
[1] Fraction Overlayer	1.000
[1] Backside Factor	1.000
Air: Refr. index	1.000
Air: Absorption	0.000
Air: N Offset	0.00000



Air: K Offset [1,1] NoName0: Thickness [nm] NoName0: N0 NoName0: N1 NoName0: N2 NoName0: K0 NoName0: K1 NoName0: K2 NoName0: N Offset NoName0: K Offset Silicon DUV-NIR: N Offset Silicon DUV-NIR: K Offset Pola.Pos. Pola.Offs. Ret.Axis Ret.Phase Eta Ana.Offs.	0.00000 39.40 1.436 40.0 0.0 0.000 0.000 0.0000 0.00000 0.00000 0.00000 45.00 0.00 0
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Ana. Offs. Lin.	0.00
Ana.Offs.Quadr.	0.00
Psi Offs. Psi Lin.	0.00 0.00
Psi Quadr.	0.00
Delta Offs.	0.00
Delta Lin.	0.00
Delta Quadr.	0.00
MSE	0.39761934

Measured Data

RRM001-047 / Psi, Delta / Spectral range: 300.2 nm - 1050.0 nm / Angle of incidence: 55.00 $^{\circ}$ / 9/17/2019 3:31:25 PM



